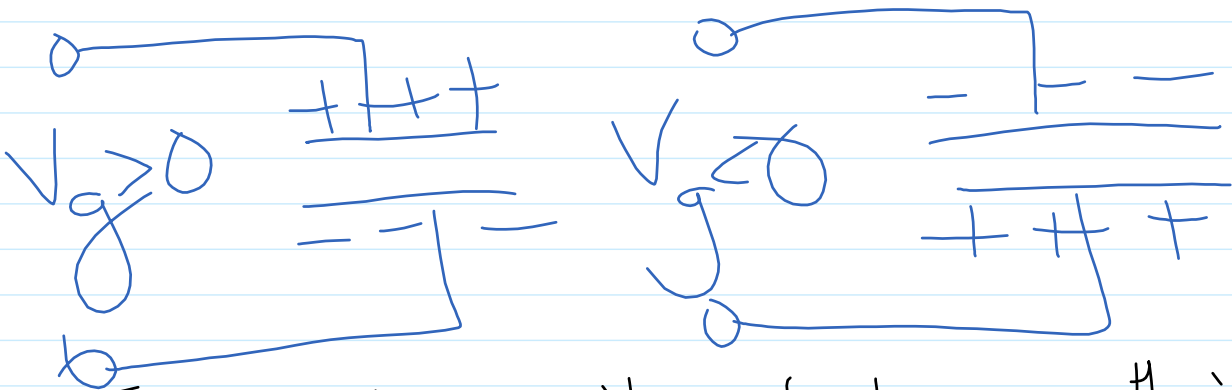
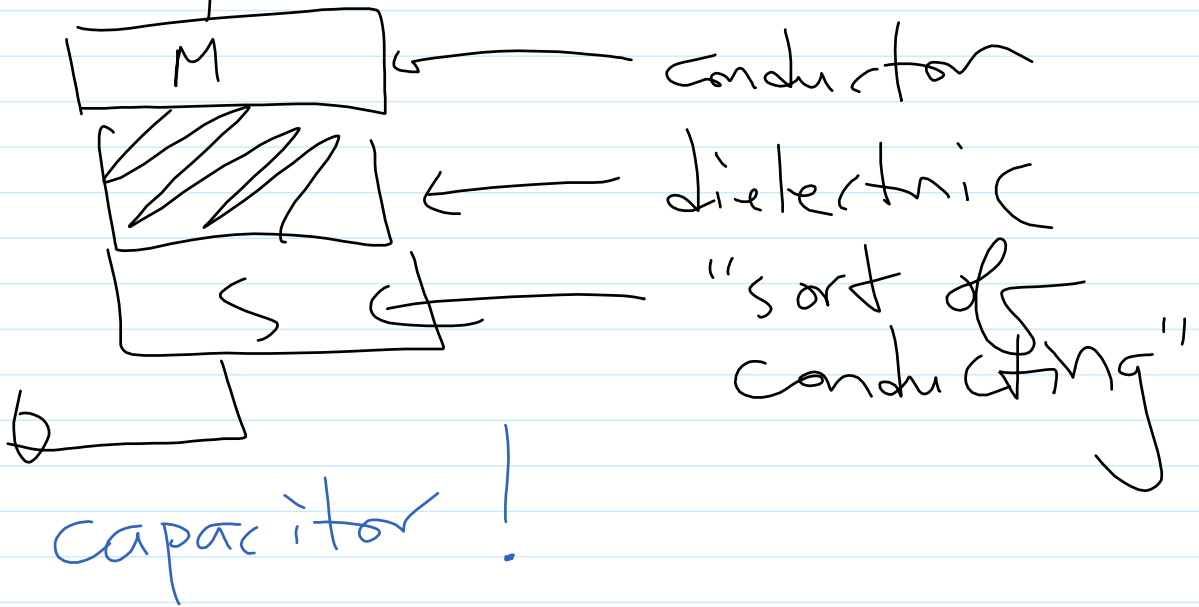
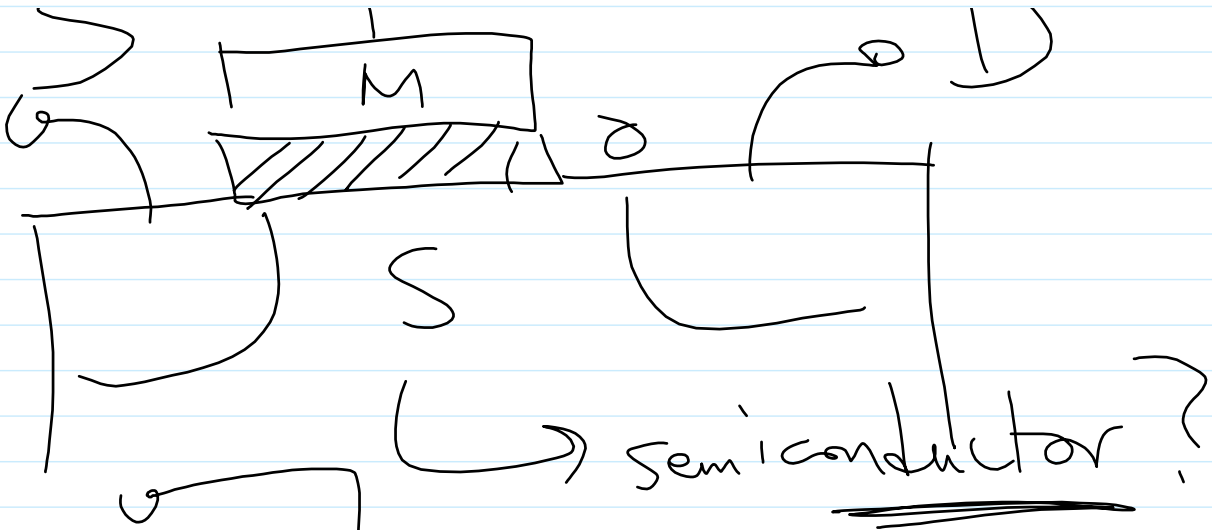


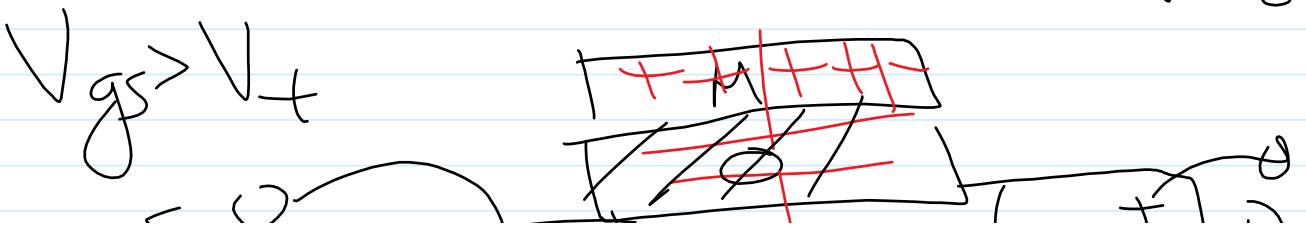
MOSFET

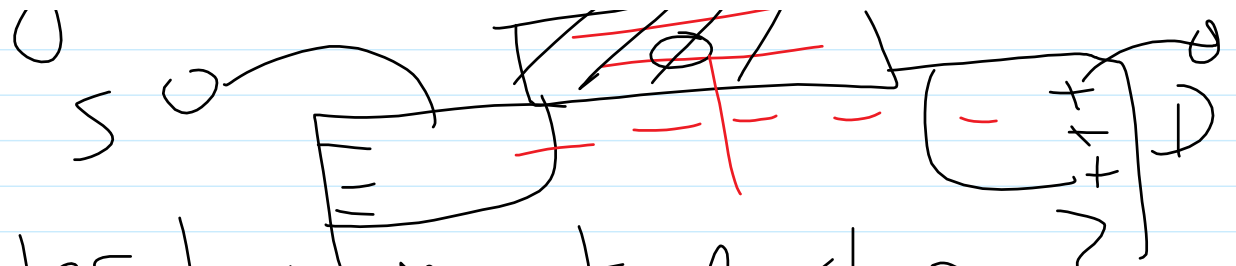
Metal oxide Semiconductor
 field-effect transistor





Transistor: similar but we think relative to V_T (threshold voltage)





lateral movement of charge?

Apply a voltage b/w D and S to push the charges along!

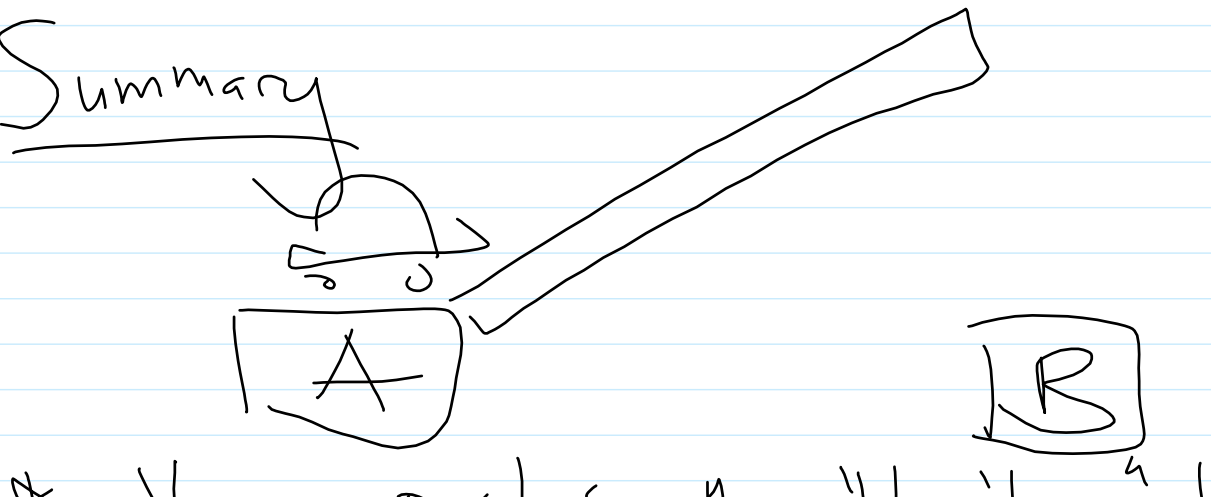
$$V_{DS} > 0$$

That was an "NMOS" transistor
 → why "N"?

negatively charged carrier

positive for PMOS

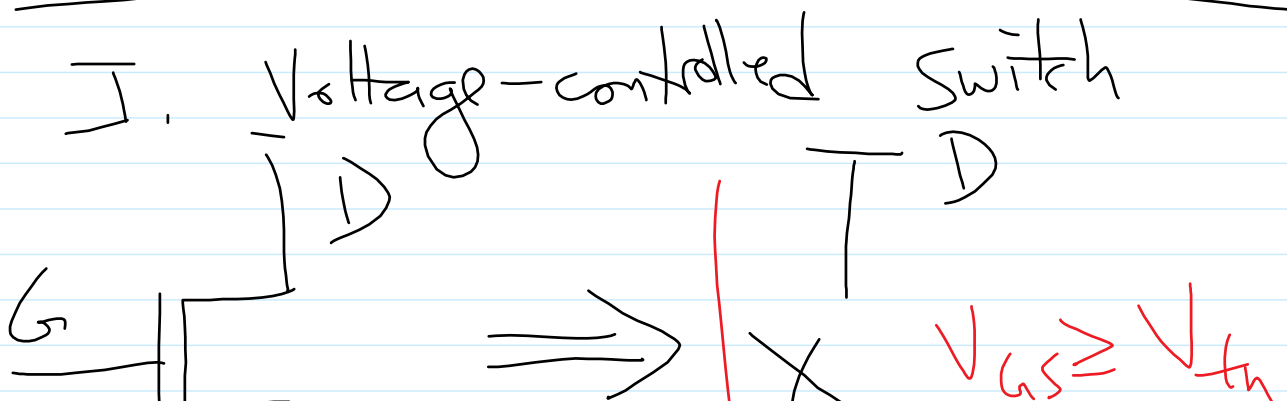
Summary

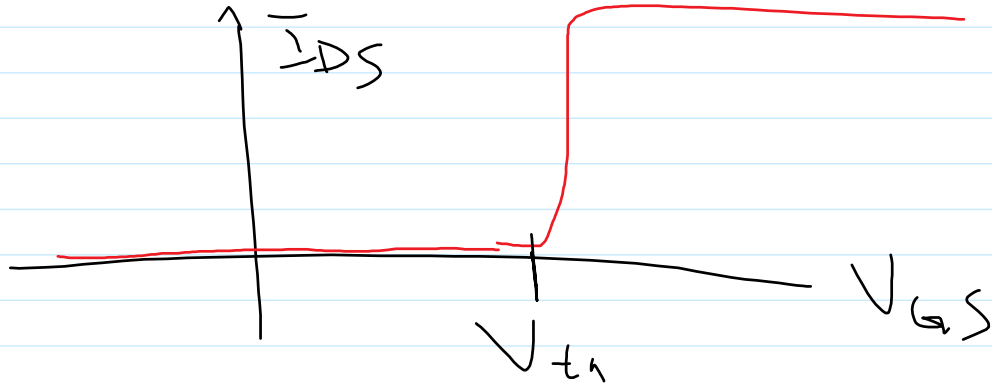
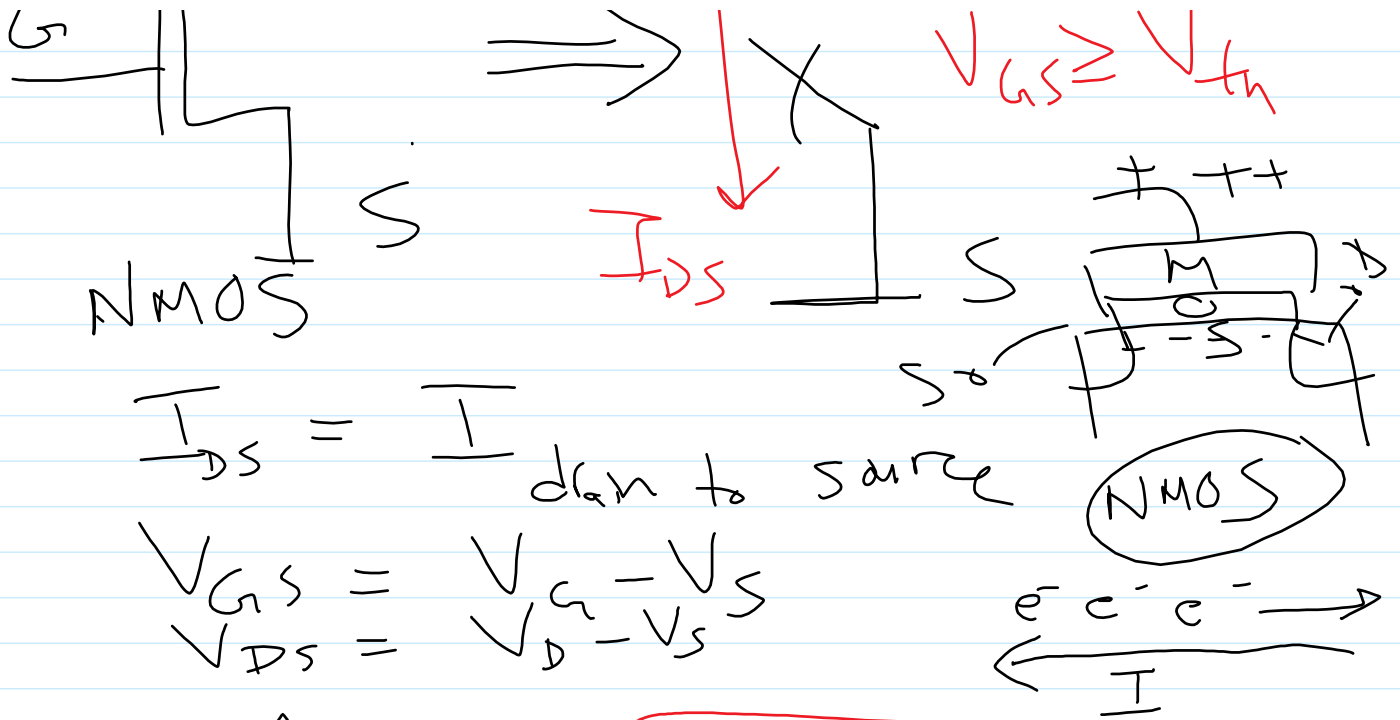


V_{GS} pushes the "bridge" down
 V_{DS} pushes the "cars" (charges)

physics \longrightarrow 1 ϕ model

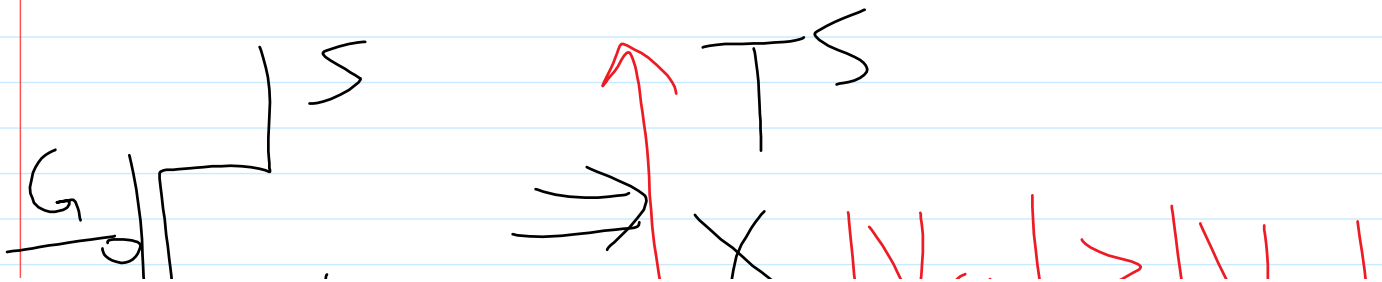
- 1 ϕ
- ① voltage-controlled switch
(most ideal; helpful for digital logic)
 - ② resistor-switch model
(helpful when thinking about power)
 - ③ RC model
(helpful for thinking about delays and transients)
- $i_c = C \frac{dV_c}{dt}$

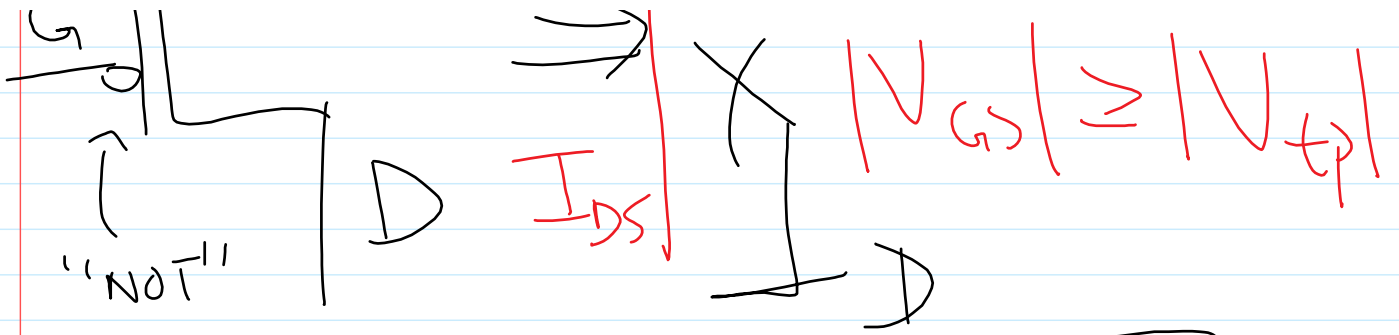




$I_{DS} > 0$ always
 $V_{th} > 0$ usually
 $V_{GS} \geq V_{th}$
 NMOS

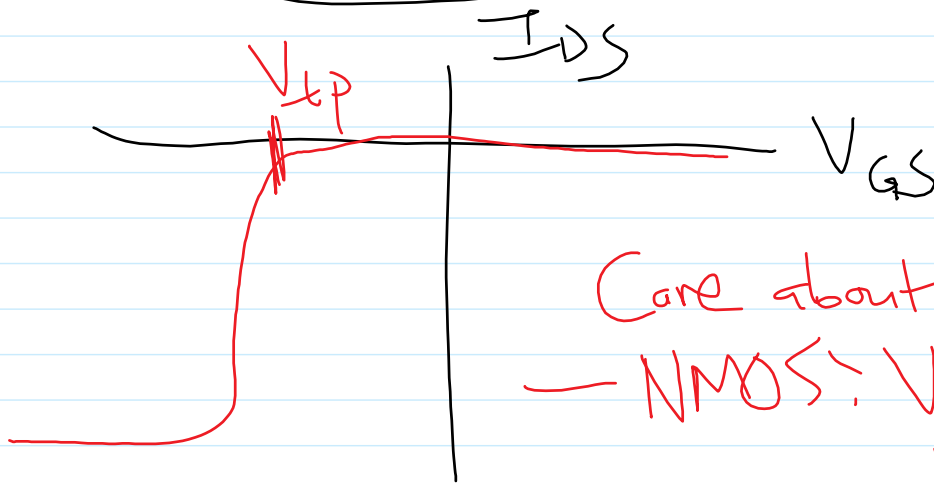
PMOS = "NOT" NMOS





$V_{tp} < 0$ almost always
 $I_{DS} < 0$ always
 $|V_{GS}| \geq |V_{tp}|$

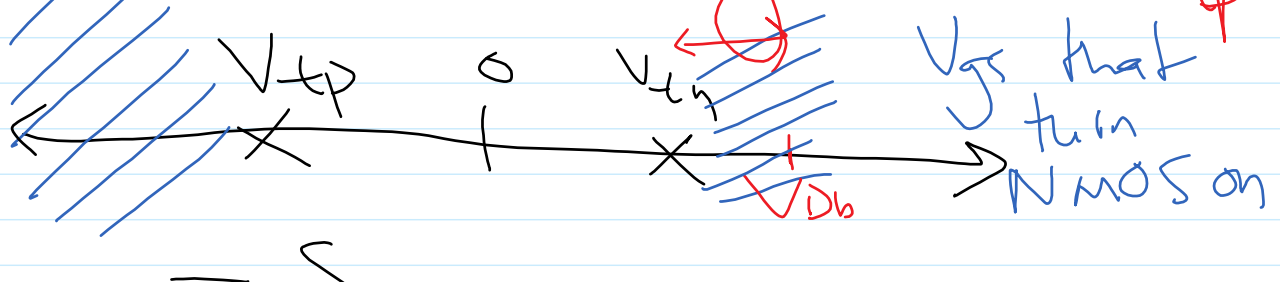
PMOS

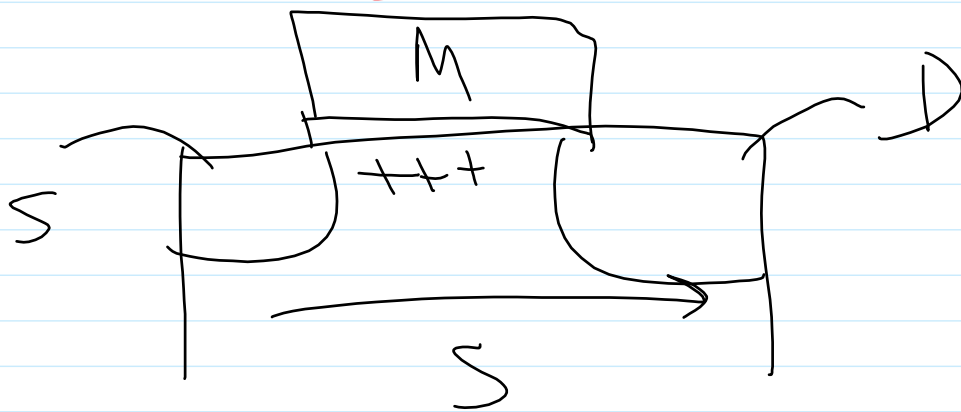
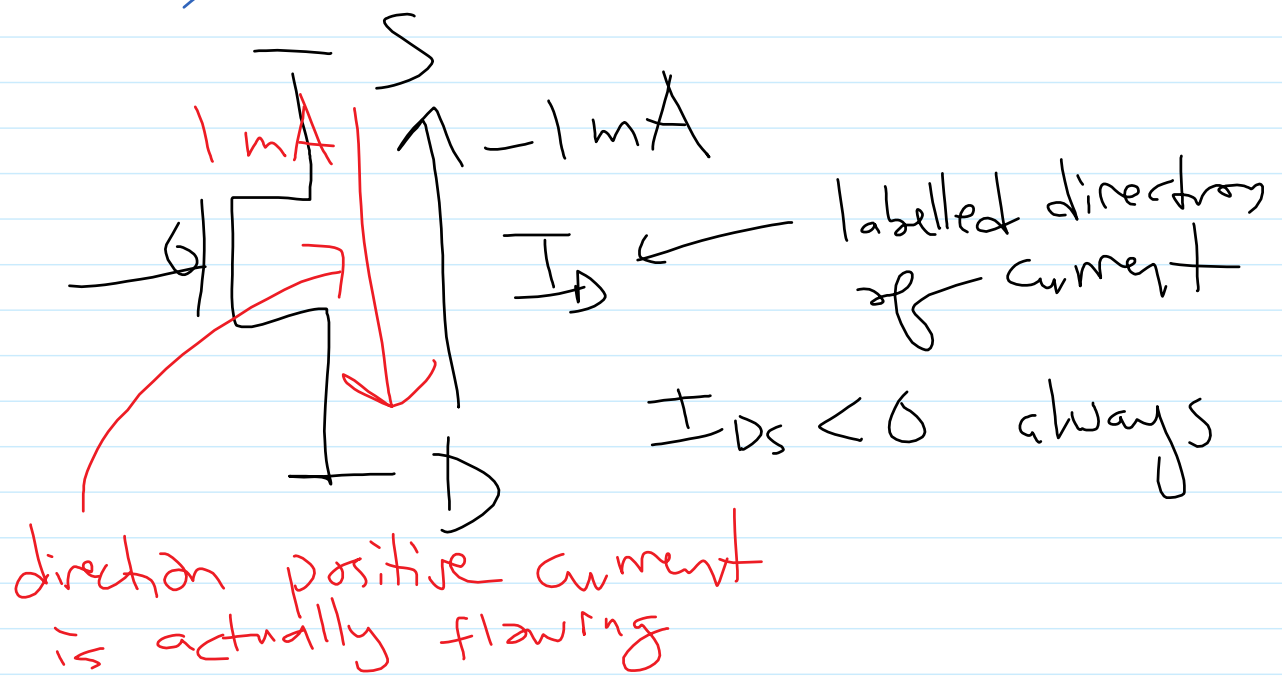


Care about the "delta":
 — NMOS: V_{GS} more positive than V_{th}

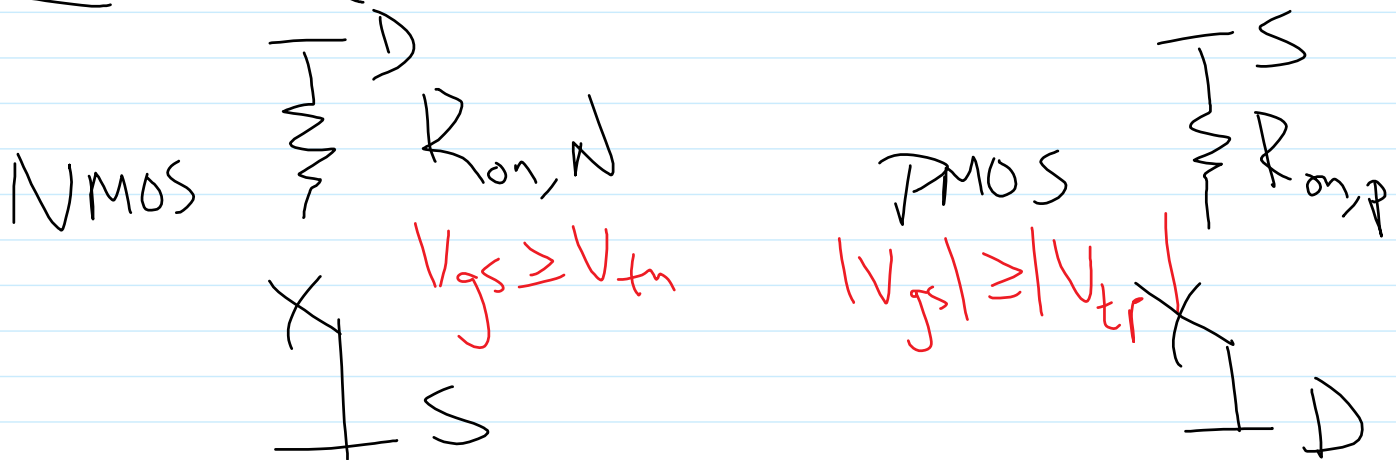
V_{GS} that turn PMOS on

— PMOS: V_{GS} more negative than V_{tp}





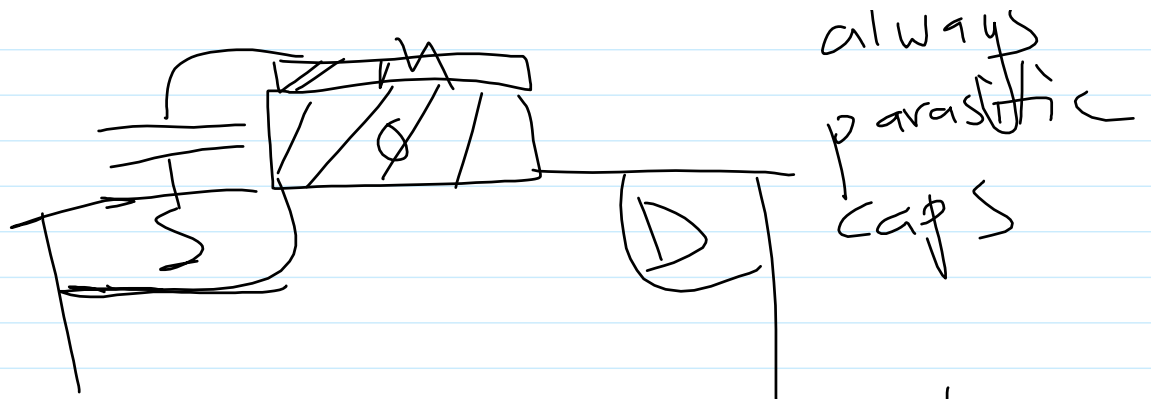
II. Resistor Switch Model



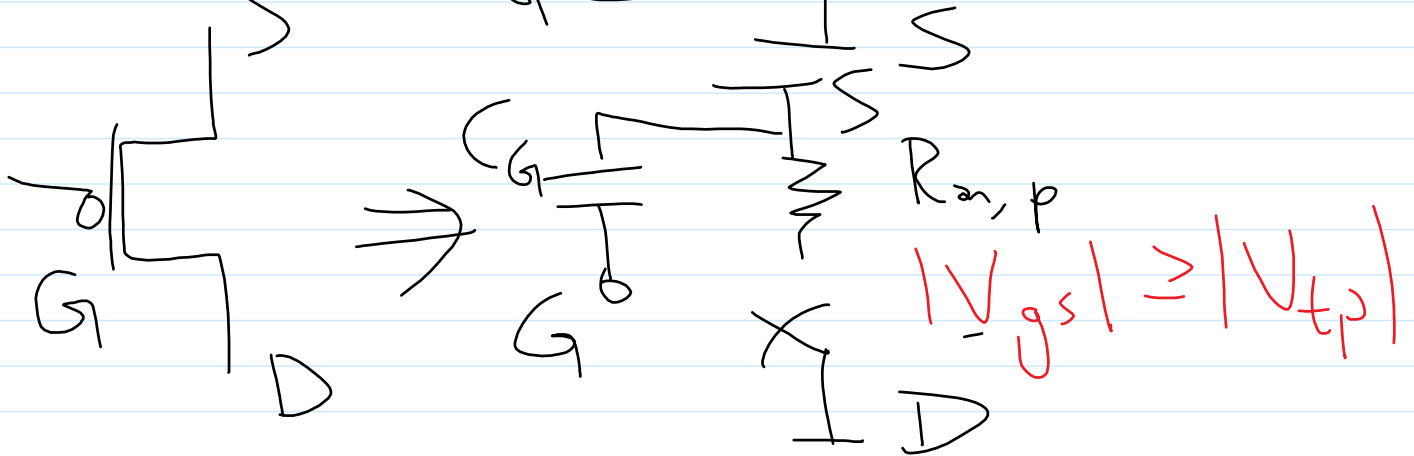
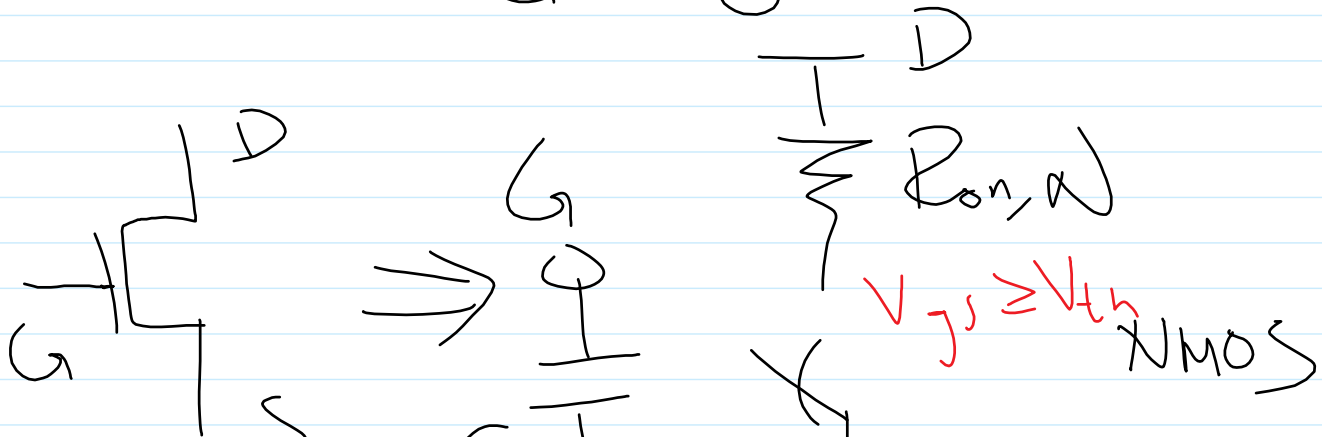
III. RC model



always



$C_G =$ gate capacitance



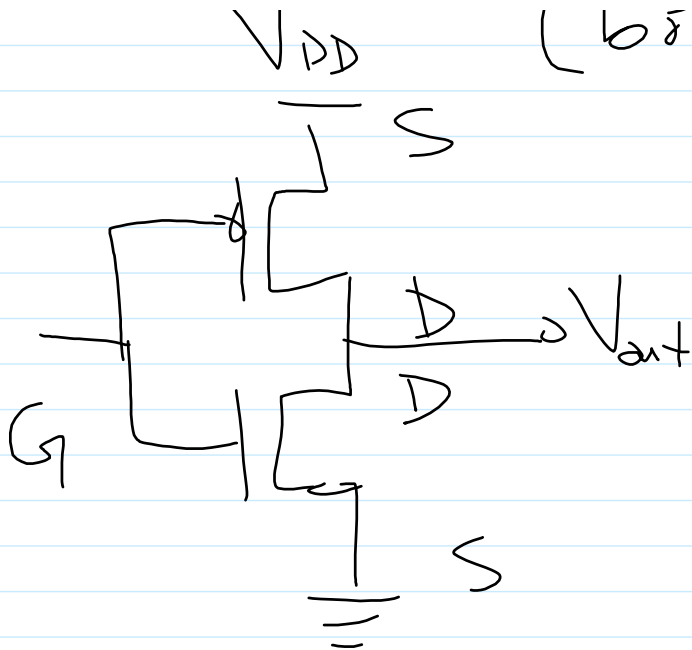
IV. CMOS inverter

complementary
(both NMOS and PMOS)

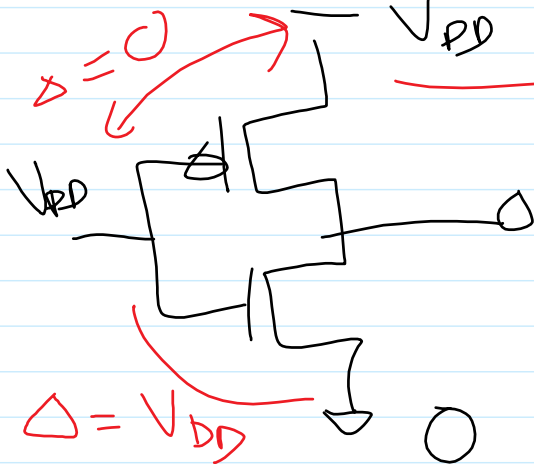
V_{DD}

(both NMOS and PMOS)

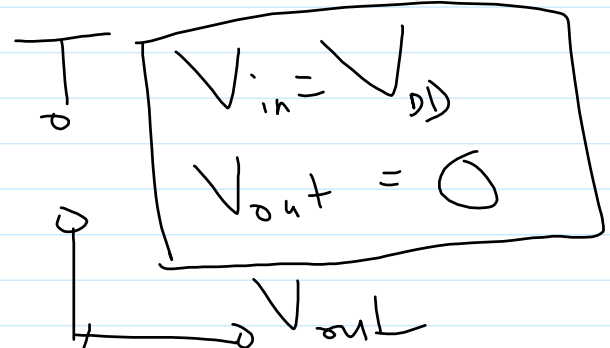
Use switch model.



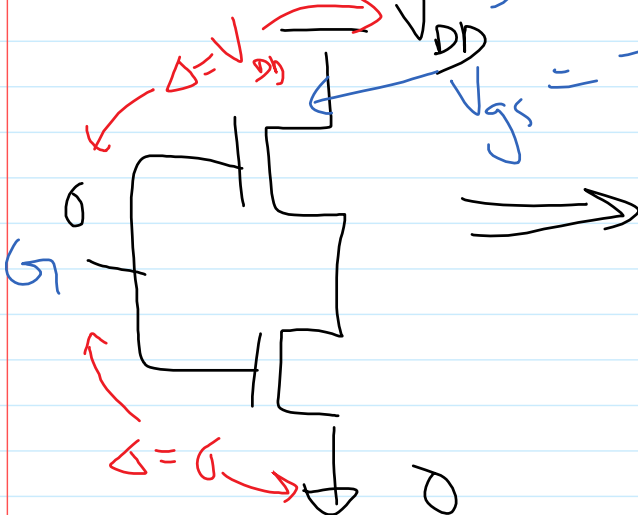
$V_{in} = V_{DD}$



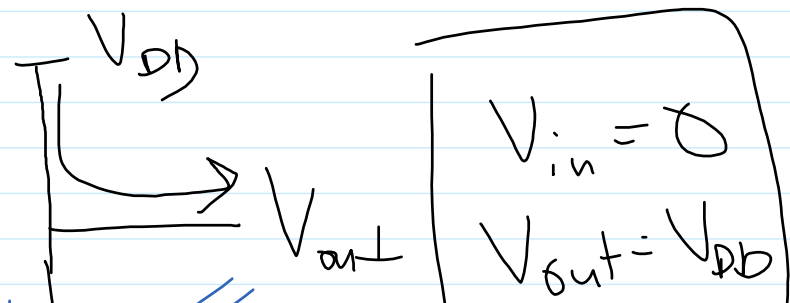
PMOS off, NMOS on



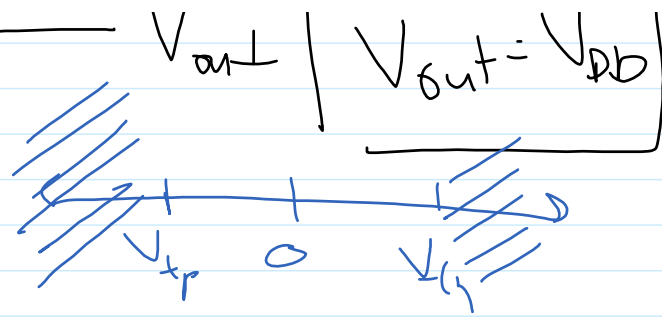
$V_{in} = 0$



PMOS on, NMOS off



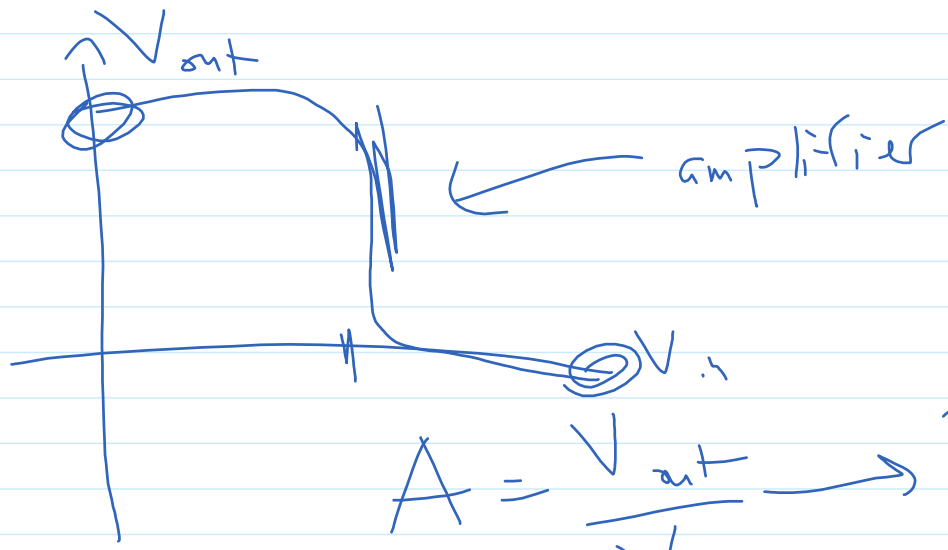
$\Delta = 0 \rightarrow 0$
 V_{gs} relative to V_{th}



Truth Table

V_{in}	V_{out}
1	0
0	1

"0" \rightarrow 0V
 "1" \rightarrow V_{DD}



$$A = \frac{V_{out}}{V_{in}} \rightarrow \frac{\partial V_{out}}{\partial V_{in}}$$

2 Single-transistor Inverter

Consider the following single-transistor inverter, consisting of an NMOS transistor and a resistor, where for N_1 we have $0 < V_{tn} < V_{DD}$.

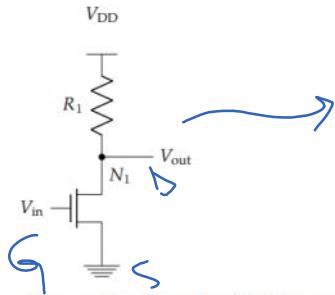


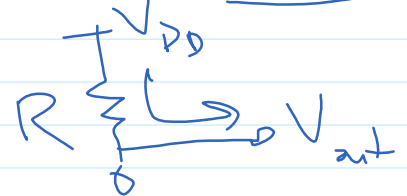
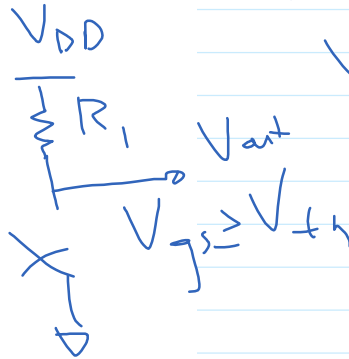
Figure 4: Single transistor NMOS inverter

a) Replace the transistor N_1 with a switch, the simplest model of a transistor and answer the following questions

- (i) What is V_{out} when $V_{in} = 0$?
- (ii) What is V_{out} when $V_{in} = V_{DD}$?
- (iii) What is the power consumption of the circuit when $V_{in} = 0$? How about when $V_{in} = V_{DD}$?

(i) $V_{in} = 0$

$V_{gs} = 0 - 0 = 0 < V_{tn}$
 NMOS off



$I = 0$
 $\Delta V = 0$
 $V_{DD} - V_{out} = 0$

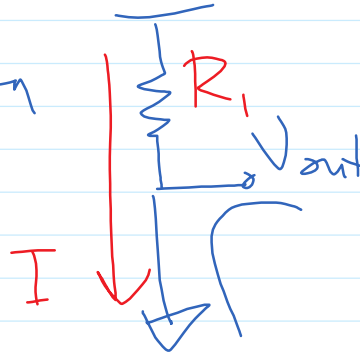
$V_{in} = 0, V_{out} = V_{DD}$

(ii) $V_{in} = V_{DD}$

$V_{gs} = V_{DD} - 0 = V_{DD} \geq V_{tn}$

NMOS is on

$V_{in} = V_{DD}, V_{out} = 0$



(iii) Power?

$V_{in} = 0: P = I V_{DD} = 0 \times V_{DD} = 0$

$P = 0$

$V_{in} = V_{DD}: I = \frac{V_{DD}}{R_1}, P = I V_{DD} = \frac{V_{DD}^2}{R_1}$

$I = 0$

$$V_{in} = V_{DD} \quad I = \frac{V_{DD}}{R_1} \quad P = IV_{DD} = \frac{V_{DD}^2}{R_1}$$

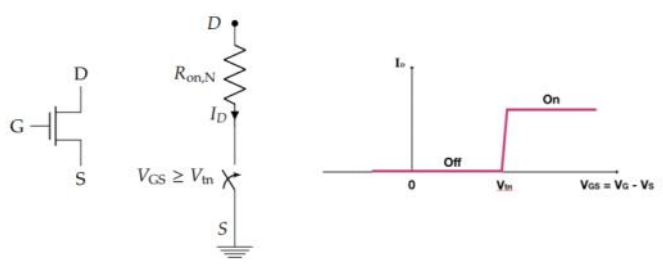
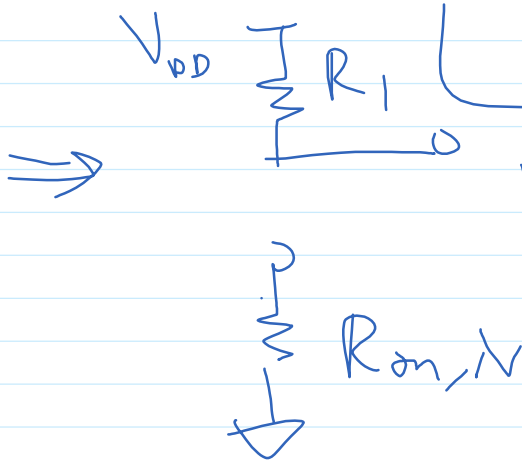
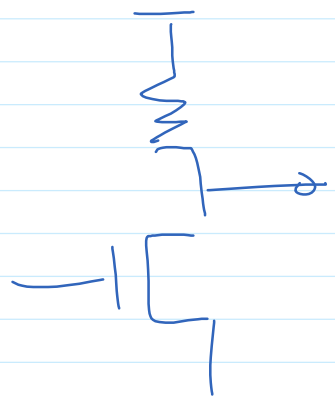


Figure 5: NMOS Transistor Resistor-switch model

- b) Now replace the NMOS device with a transistor model that includes an internal resistor, such as the one in the figure above.
- (i) What is V_{out} when $V_{in} = 0$?
 - (ii) What is V_{out} when $V_{in} = V_{DD}$ in terms of R_1 and $R_{on,N}$?
What is this value if $R_{on,N} = \frac{1}{10}R_1$?
How much power does the circuit consume?

(b) Resistor-Switch Model

(i) $V_{in} = 0, V_{GS} = 0 - 0 = 0 < V_{th}$
NMOS off



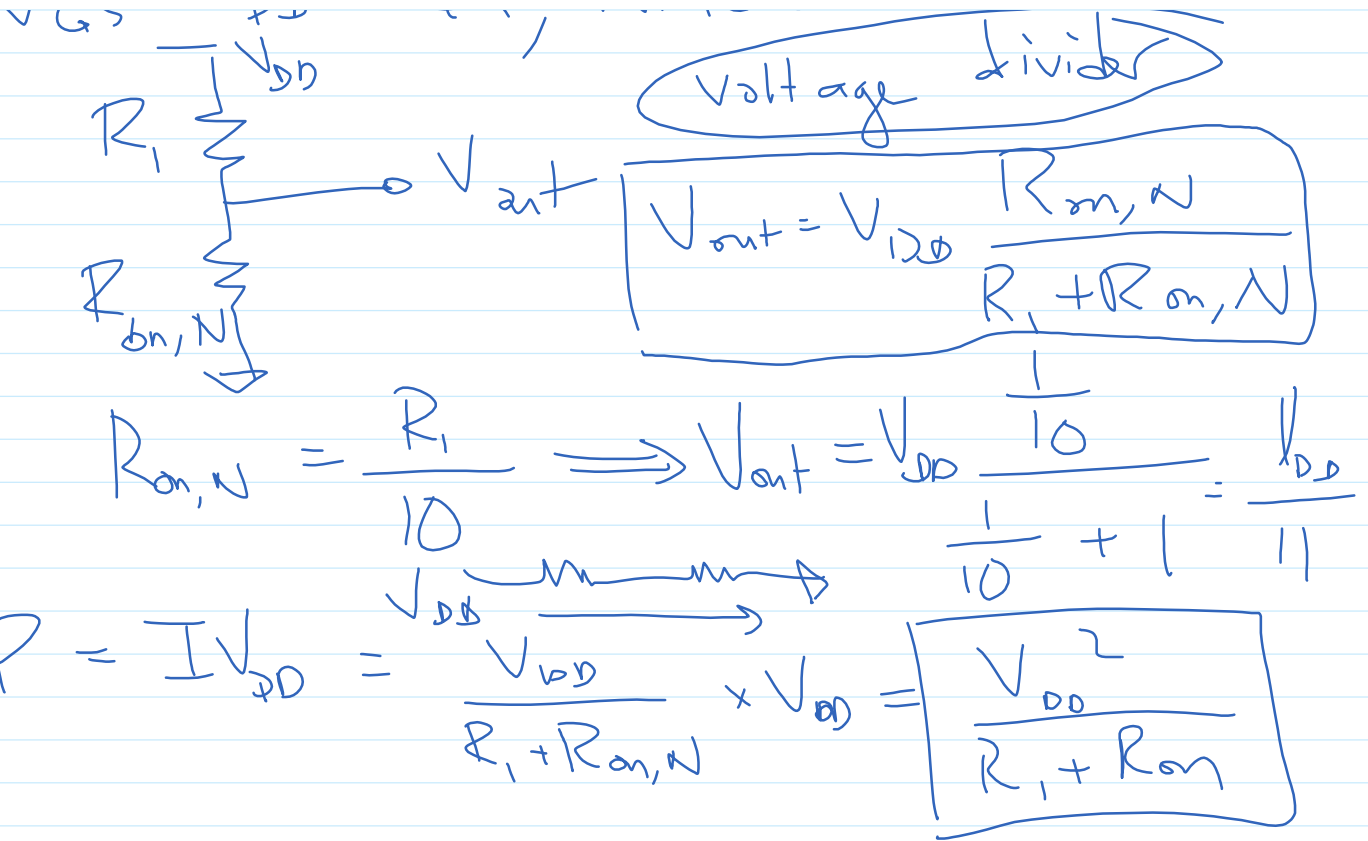
$$V_{in} = 0$$

$$V_{out} = V_{DD}$$

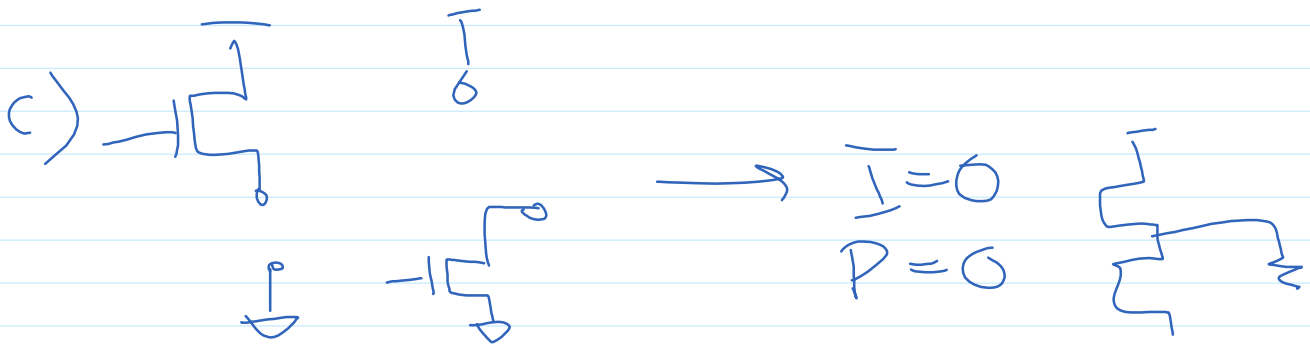
$$P = 0$$

(ii) $V_{in} = V_{DD}$

$V_{GS} = V_{DD} > V_{th}$, NMOS on
Voltage divider



c) Now consider a CMOS inverter with both PMOS and CMOS devices, such as that of Figure 3. How does the performance and power consumption compare?



3 NAND Circuit

Let us consider a NAND logic gate. This circuit implements the boolean function $\overline{(A \cdot B)}$.

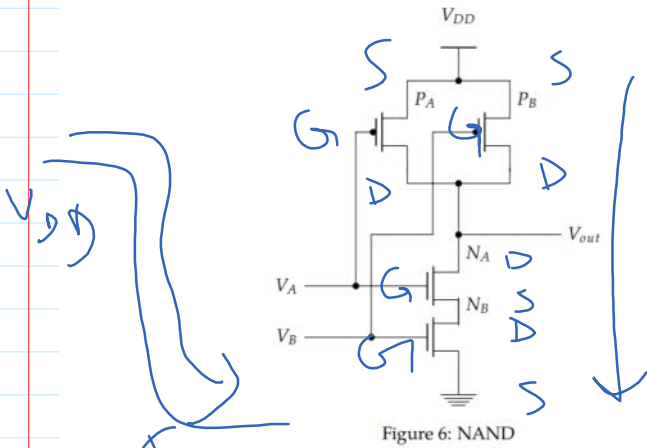


Figure 6: NAND

V_{tn} and V_{tp} are the threshold voltages for the NMOS and PMOS transistors, respectively. Assume that $V_{DD} > V_{tn}$ and $|V_{tp}| > 0$.

a) Label the gate, source, and drain nodes for the NMOS and PMOS transistors above.

a) Label nodes.
 gates — floating thingy
 S/D: NMOS — $I_{DS} > 0$
 positive current flows from
 D to S — $V_D > V_S$

PMOS — $I_{DS} < 0$
 $V_S > V_D$

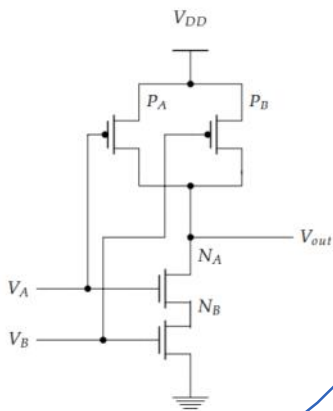


Figure 7: NAND

$\overline{(A \cdot B)}$ = not and = nand
 Expect

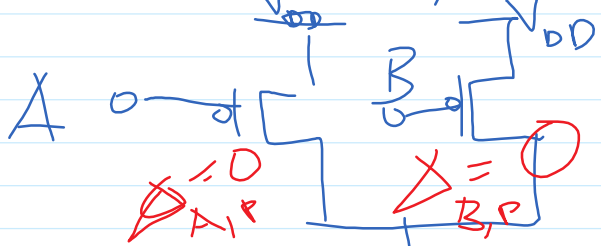
A	B	Out
1	1	0
0	1	1
1	0	1
0	0	1

- b) If $V_A = V_{DD}$ and $V_B = V_{DD}$, which transistors act like open circuits? Which transistors act like closed circuits? What is V_{out} ?
- c) If $V_A = 0V$ and $V_B = V_{DD}$, what is V_{out} ?
- d) If $V_A = V_{DD}$ and $V_B = 0V$, what is V_{out} ?
- e) If $V_A = 0V$ and $V_B = 0V$, what is V_{out} ?

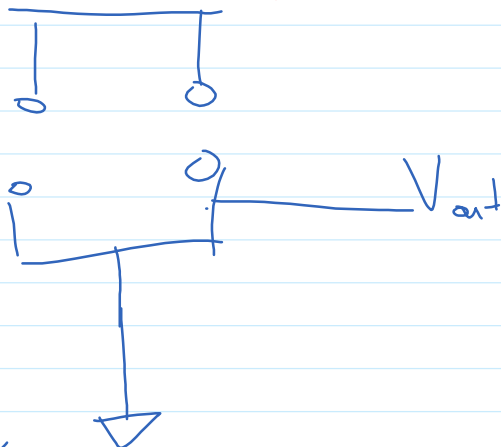
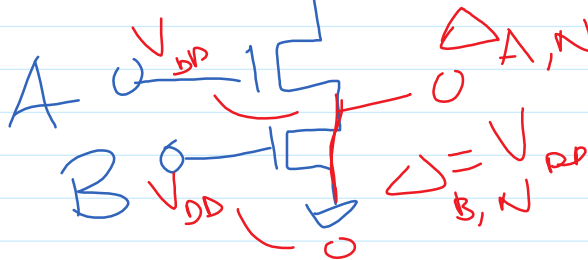
a) $V_A = V_{DD}$ / $V_B = V_{DD}$

. DMM AS AR

a) $V_A = V_{DD} / V_B = V_{DD}$

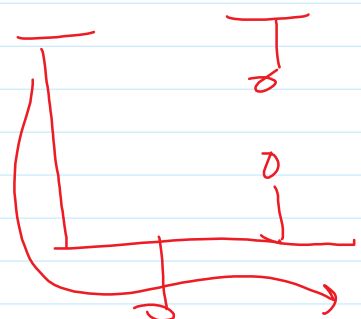
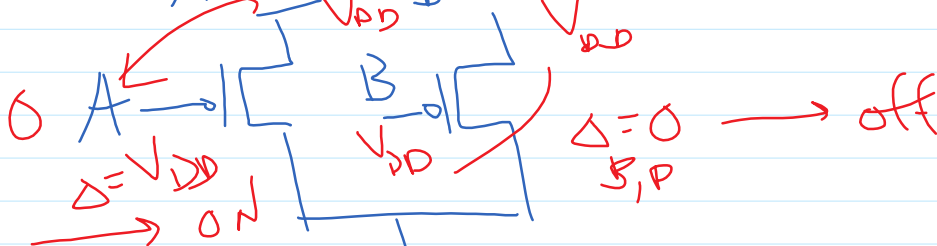


PMOS A, B
off
NMOS A, B
on



$V_{out} = 0$
 $V_A = V_{DD} / V_B = V_{DD}$
"1" "1"

b) $V_A = 0 / V_B = V_{DD}$



$V_A = 0, V_B = V_{DD}$
 $V_{out} = V_{DD}$

c) $V_A = V_{DD} / V_B = 0$

